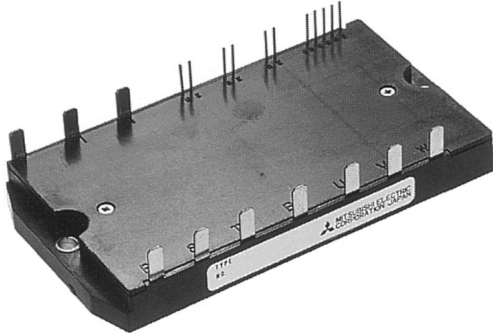


# CM25MD-24H

## MEDIUM POWER SWITCHING USE INSULATED TYPE

# CM25MD-24H



- IC ..... 25A
- VCES ..... 1200V
- Insulated Type
- CIB Module  
3 $\phi$  Inverter+3 $\phi$  Converter+Brake
- UL Recognized

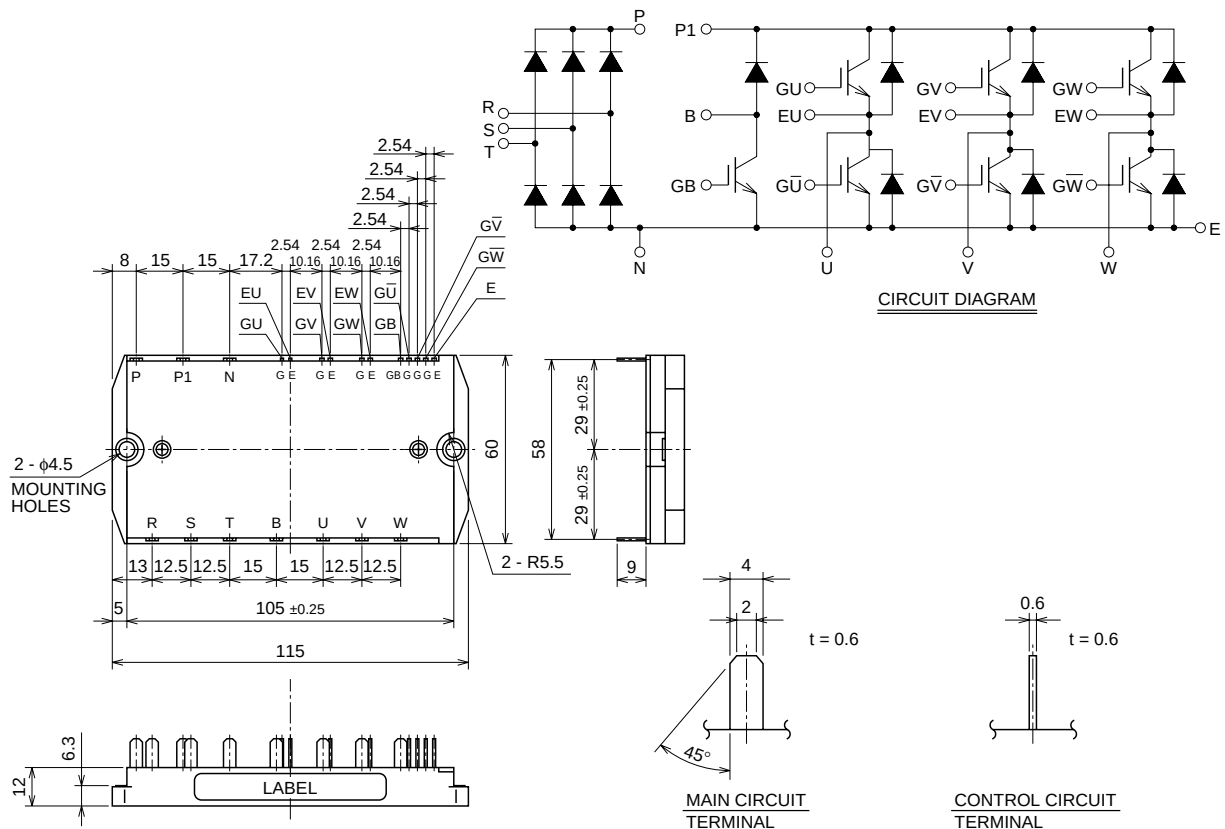
Yellow Card No. E80276 (N)  
File No. E80271

## APPLICATION

AC & DC motor controls, General purpose inverters, Servo controls, NC, Robotics

### OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



# CM25MD-24H

MEDIUM POWER SWITCHING USE  
INSULATED TYPE

## MAXIMUM RATINGS (T<sub>j</sub> = 25°C) INVERTER PART

| Symbol                    | Parameter                     | Condition             | Rating | Unit |
|---------------------------|-------------------------------|-----------------------|--------|------|
| V <sub>CES</sub>          | Collector-emitter voltage     | G – E Short           | 1200   | V    |
| V <sub>GES</sub>          | Gate-emitter voltage          | C – E Short           | ±20    | V    |
| I <sub>C</sub>            | Collector Current             | T <sub>c</sub> = 25°C | 25     | A    |
| I <sub>CM</sub>           |                               | PULSE (Note. 2)       | 50     | A    |
| I <sub>E</sub> (Note. 1)  | Emitter Current               | T <sub>c</sub> = 25°C | 25     | A    |
| I <sub>EM</sub> (Note. 1) |                               | PULSE (Note. 2)       | 50     | A    |
| P <sub>C</sub> (Note. 3)  | Maximum collector dissipation | T <sub>f</sub> = 25°C | 104    | W    |

## BRAKE PART

| Symbol                    | Parameter                       | Condition             | Rating | Unit |
|---------------------------|---------------------------------|-----------------------|--------|------|
| V <sub>CES</sub>          | Collector-emitter voltage       | G – E Short           | 1200   | V    |
| V <sub>GES</sub>          | Gate-emitter voltage            | C – E Short           | ±20    | V    |
| I <sub>C</sub>            | Collector Current               | T <sub>c</sub> = 25°C | 25     | A    |
| I <sub>CM</sub>           |                                 | PULSE (Note. 2)       | 50     | A    |
| P <sub>C</sub> (Note. 3)  | Maximum Collector dissipation   | T <sub>f</sub> = 25°C | 104    | W    |
| V <sub>RRM</sub>          | Repetitive peak reverse voltage | Clamp diode part      | 1200   | V    |
| I <sub>FM</sub> (Note. 3) | Forward current                 | Clamp diode part      | 25     | A    |

## CONVERTER PART

| Symbol           | Parameter                              | Condition                                  | Rating | Unit             |
|------------------|----------------------------------------|--------------------------------------------|--------|------------------|
| V <sub>RRM</sub> | Repetitive peak reverse voltage        |                                            | 1600   | V                |
| E <sub>a</sub>   | Recommended AC input voltage           |                                            | 440    | V                |
| I <sub>O</sub>   | DC output current                      | 3φ rectifying circuit                      | 25     | A                |
| I <sub>FSM</sub> | Surge (non-repetitive) forward current | 1 cycle at 60Hz, peak value Non-repetitive | 250    | A                |
| I <sup>2</sup> t | I <sup>2</sup> t for fusing            | Value for one cycle of surge current       | 260    | A <sup>2</sup> s |

## COMMON RATING

| Symbol           | Parameter            | Condition         | Rating     | Unit |
|------------------|----------------------|-------------------|------------|------|
| T <sub>j</sub>   | Junction temperature |                   | –40 ~ +150 | °C   |
| T <sub>stg</sub> | Storage temperature  |                   | –40 ~ +125 | °C   |
| V <sub>iso</sub> | Isolation voltage    | AC 1 min.         | 2500       | V    |
| —                | Mounting torque      | Mounting M4 screw | 0.98 ~1.47 | N·m  |
| —                | Weight               | Typical value     | 100        | g    |

## CM25MD-24H

MEDIUM POWER SWITCHING USE  
INSULATED TYPEELECTRICAL CHARACTERISTICS ( $T_j = 25^\circ\text{C}$ )

## INVERTER PART

| Symbol                   | Parameter                            | Test conditions                          | Limits |      |      | Unit               |
|--------------------------|--------------------------------------|------------------------------------------|--------|------|------|--------------------|
|                          |                                      |                                          | Min.   | Typ. | Max. |                    |
| ICES                     | Collector cutoff current             | $V_{CE} = V_{CES}, V_{GE} = 0V$          | —      | —    | 1    | mA                 |
| $V_{GE(th)}$             | Gate-emitter threshold voltage       | $I_C = 2.5mA, V_{CE} = 10V$              | 4.5    | 6    | 7.5  | V                  |
| IGES                     | Gate-emitter cutoff current          | $V_{GE} = V_{GES}, V_{CE} = 0V$          | —      | —    | 0.5  | $\mu A$            |
| $V_{CE(sat)}$            | Collector-emitter saturation voltage | $T_j = 25^\circ\text{C}$                 | —      | 2.7  | 3.4  | V                  |
|                          |                                      | $T_j = 150^\circ\text{C}$                | —      | 2.45 | —    |                    |
| Cies                     | Input capacitance                    | $V_{CE} = 10V$<br>$V_{GE} = 0V$          | —      | —    | 5.0  | nF                 |
| Coes                     | Output capacitance                   |                                          | —      | —    | 3.8  | nF                 |
| Cres                     | Reverse transfer capacitance         |                                          | —      | —    | 1.0  | nF                 |
| QG                       | Total gate charge                    | $V_{CC} = 600V, I_C = 25A, V_{GE} = 15V$ | —      | 125  | —    | nC                 |
| $t_d(on)$                | Turn-on delay time                   | $V_{CC} = 600V, I_C = 25A$               | —      | —    | 100  | ns                 |
| $t_r$                    | Turn-on rise time                    | $V_{GE1} = V_{GE2} = 15V$                | —      | —    | 200  | ns                 |
| $t_d(off)$               | Turn-off delay time                  | $R_G = 13\Omega$                         | —      | —    | 150  | ns                 |
| $t_f$                    | Turn-off fall time                   | Resistive load                           | —      | —    | 350  | ns                 |
| $V_{EC}$ (Note. 1)       | Emitter-collector voltage            | $I_E = 25A, V_{GE} = 0V$                 | —      | —    | 3.5  | V                  |
| $t_{rr}$ (Note. 1)       | Reverse recovery time                | $I_E = 25A, V_{GE} = 0V$                 | —      | —    | 250  | ns                 |
| $Q_{rr}$ (Note. 1)       | Reverse recovery charge              | $di_e / dt = -50A / \mu s$               | —      | 0.22 | —    | $\mu C$            |
| $R_{th(j-f)Q}$ (Note. 5) | Thermal resistance                   | IGBT part, Per 1/6 module                | —      | —    | 1.2  | $^\circ\text{C/W}$ |
| $R_{th(j-f)R}$ (Note. 5) |                                      | FWDi part, Per 1/6 module                | —      | —    | 1.9  | $^\circ\text{C/W}$ |

## BRAKE PART

| Symbol                   | Parameter                               | Condition                                | Limits |      |      | Unit               |
|--------------------------|-----------------------------------------|------------------------------------------|--------|------|------|--------------------|
|                          |                                         |                                          | Min.   | Typ. | Max. |                    |
| ICES                     | Collector cutoff current                | $V_{CE} = V_{CES}, V_{GE} = 0V$          | —      | —    | 1    | mA                 |
| $V_{GE(th)}$             | Gate-emitter threshold voltage          | $I_C = 2.5mA, V_{CE} = 10V$              | 4.5    | 6    | 7.5  | V                  |
| IGES                     | Gate-emitter cutoff current             | $V_{GE} = V_{GES}, V_{CE} = 0V$          | —      | —    | 0.5  | $\mu A$            |
| $V_{CE(sat)}$            | Collector-to-emitter saturation voltage | $T_j = 25^\circ\text{C}$                 | —      | 2.7  | 3.4  | V                  |
|                          |                                         | $T_j = 150^\circ\text{C}$                | —      | 2.45 | —    |                    |
| Cies                     | Input capacitance                       | $V_{CE} = 10V$<br>$V_{GE} = 0V$          | —      | —    | 5.0  | nF                 |
| Coes                     | Output capacitance                      |                                          | —      | —    | 3.8  | nF                 |
| Cres                     | Reverse transfer capacitance            |                                          | —      | —    | 1.0  | nF                 |
| QG                       | Total gate charge                       | $V_{CC} = 600V, I_C = 25A, V_{GE} = 15V$ | —      | 125  | —    | nC                 |
| $V_{FM}$                 | Forward voltage drop                    | $I_F = 25A$ , Clamp diode part           | —      | —    | 1.5  | V                  |
| $R_{th(j-f)Q}$ (Note. 5) | Thermal resistance                      | IGBT part                                | —      | —    | 1.2  | $^\circ\text{C/W}$ |
| $R_{th(j-f)R}$ (Note. 5) |                                         | Clamp diode part                         | —      | —    | 1.7  | $^\circ\text{C/W}$ |

## CONVERTER PART

| Symbol                  | Parameter                  | Condition                                | Limits |      |      | Unit               |
|-------------------------|----------------------------|------------------------------------------|--------|------|------|--------------------|
|                         |                            |                                          | Min.   | Typ. | Max. |                    |
| IRRM                    | Repetitive reverse current | $V_R = V_{RRM}, T_j = 150^\circ\text{C}$ | —      | —    | 8    | mA                 |
| $V_{FM}$                | Forward voltage drop       | $I_F = 25A$                              | —      | —    | 1.5  | V                  |
| $R_{th(j-f)}$ (Note. 5) | Thermal resistance         | Per 1/6 module                           | —      | —    | 1.7  | $^\circ\text{C/W}$ |

Note 1.  $I_E$ ,  $V_{EC}$ ,  $t_{rr}$ ,  $Q_{rr}$  &  $di_e/dt$  represent characteristics of the anti-parallel, emitter to collector free-wheel diode.2. Pulse width and repetition rate should be such that the device junction temp. ( $T_j$ ) does not exceed  $T_{jmax}$  rating.3. Junction temperature ( $T_j$ ) should not increase beyond  $150^\circ\text{C}$ .

4. Pulse width and repetition rate should be such as to cause negligible temperature rise.

5. Thermal resistance is specified under following conditions.

• The conductive grease applied, between module and fin.

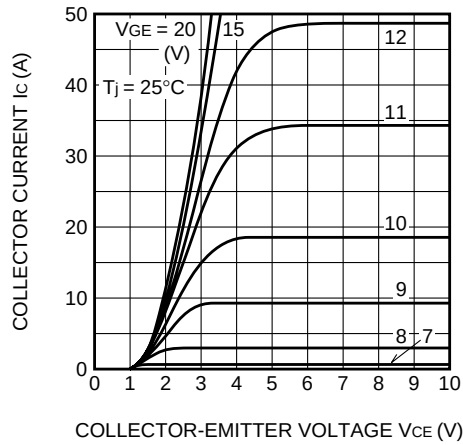
• Al plate is used as fin.

# CM25MD-24H

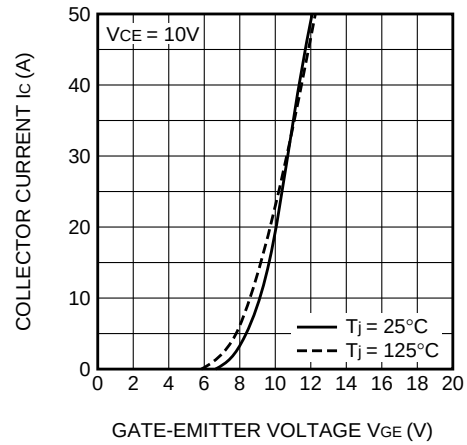
MEDIUM POWER SWITCHING USE  
INSULATED TYPE

## PERFORMANCE CURVES

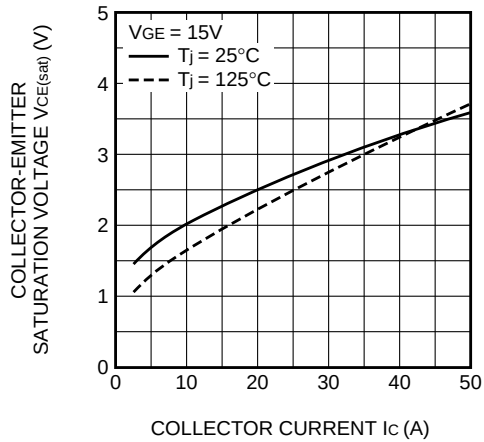
OUTPUT CHARACTERISTICS  
(TYPICAL)



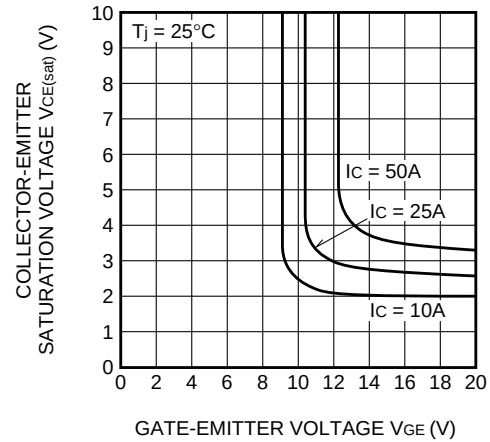
TRANSFER CHARACTERISTICS  
(TYPICAL)



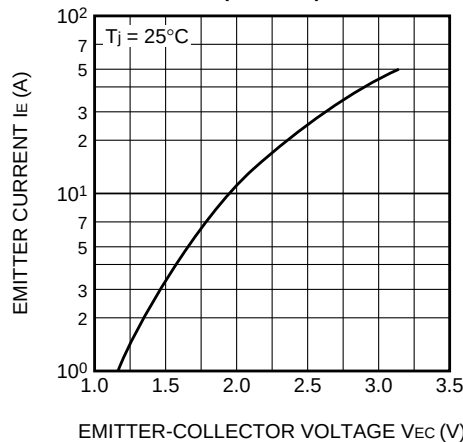
COLLECTOR-EMITTER SATURATION  
VOLTAGE CHARACTERISTICS  
(TYPICAL)



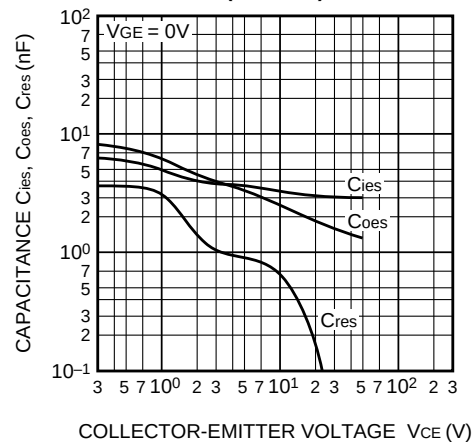
COLLECTOR-EMITTER SATURATION  
VOLTAGE CHARACTERISTICS  
(TYPICAL)



FREE-WHEEL DIODE  
FORWARD CHARACTERISTICS  
(TYPICAL)



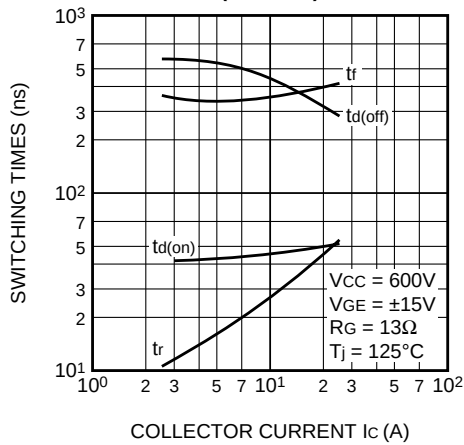
CAPACITANCE VS.  $V_{ce}$   
(TYPICAL)



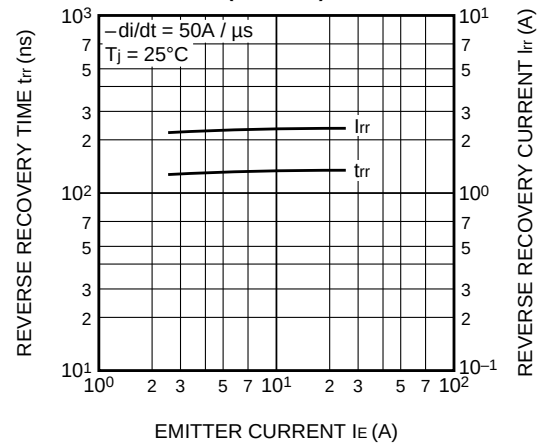
# CM25MD-24H

MEDIUM POWER SWITCHING USE  
INSULATED TYPE

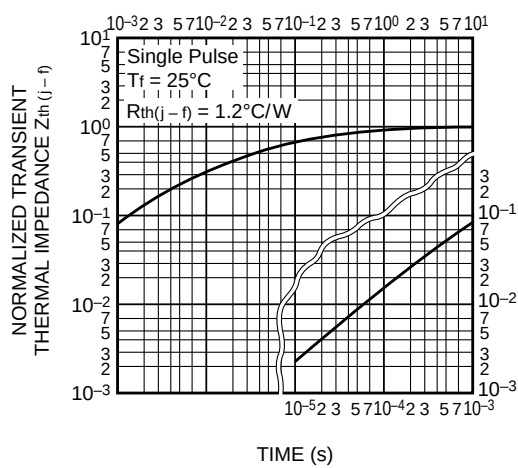
HALF-BRIDGE  
SWITCHING CHARACTERISTICS  
(TYPICAL)



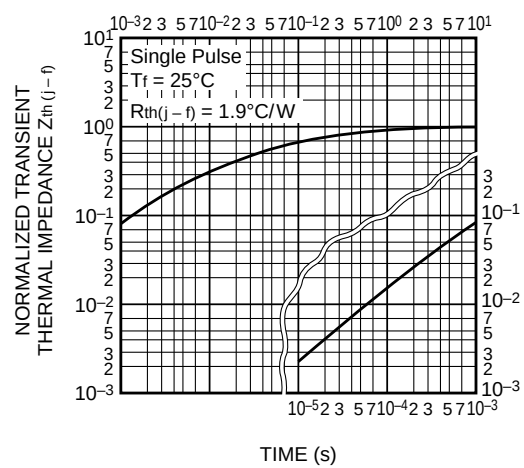
REVERSE RECOVERY CHARACTERISTICS  
OF FREE-WHEEL DIODE  
(TYPICAL)



TRANSIENT THERMAL  
IMPEDANCE CHARACTERISTICS  
(IGBT part)



TRANSIENT THERMAL  
IMPEDANCE CHARACTERISTICS  
(FWDi part)



$V_{GE}$  - GATE CHARGE  
(TYPICAL)

